

**In The Claims:**

Please cancel Claim 51 without prejudice and without disclaimer of subject matter.

Please amend Claims 23 and 24 as follows:

23. (Currently Amended) A trench DMOS made in accordance with the following method:

providing an article comprising a substrate of a first conductivity type and a body region of a second conductivity type, said article having a trench which extends through said body region and into said substrate;

depositing a gate oxide layer in the trench;

forming a gate in the trench, said gate having a first layer comprising undoped polysilicon, a second layer comprising doped polysilicon, and a third ~~at least one~~ layer comprising a material selected from the group consisting of polycide and refractory metals; and forming a source region in the body region;

wherein the source region is formed after the gate oxide layer is deposited, and

wherein said source region is formed with a junction depth of less than about 0.5  $\mu\text{m}$ ,

said trench DMOS comprising a plurality of gate electrodes, and wherein each of said gate electrodes has a BPSG region extending over a top portion of the gate ~~associated with it~~.

24. (Currently Amended) A trench DMOS made in accordance with the following method:

providing an article comprising a substrate of a first conductivity type and a body region of a second conductivity type, said article having a trench which extends through said body region and into said substrate;

depositing a gate oxide layer in the trench;

forming a gate in the trench, said gate having a first layer comprising undoped polysilicon, a second layer comprising doped polysilicon, and a third at least one layer comprising a material selected from the group consisting of polycide and refractory metals; and

forming a source region in the body region;

wherein the source region is formed after the gate oxide layer is deposited.

25. (Original) The trench DMOS of claim 24, further comprising a drain, wherein the distance between at least a portion of said gate and said drain is greater than the distance between said source region and said drain.

59. (Canceled)